

Maxime Berthou

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Planar edge terminations for high voltage 4H-SiC power MOSFETs. <i>Semiconductor Science and Technology</i> , 2017, 32, 035007.	1.0	6
2	High-Voltage 4H-SiC Power MOSFETs With Boron-Doped Gate Oxide. <i>IEEE Transactions on Industrial Electronics</i> , 2017, 64, 8962-8970.	5.2	19
3	Repetitive Short-Circuit Tests on SiC VMOS Devices. <i>Materials Science Forum</i> , 2016, 858, 812-816.	0.3	5
4	An Ultrafast I-V Measurement Technique Accounting for Capacitive and Leakage Currents in Reverse Mode for SiC Power Devices. <i>Materials Science Forum</i> , 2016, 858, 422-425.	0.3	0
5	Design Impact on the Static and Short-Circuit Characteristics of SiC-SIT with Non-Uniformly Doped Channel. <i>Materials Science Forum</i> , 2016, 858, 925-928.	0.3	0
6	Modeling of Inhomogeneous 4H-SiC Schottky and JBS Diodes in a Wide Temperature Range. <i>Materials Science Forum</i> , 2016, 858, 741-744.	0.3	3
7	Gate Oxide Degradation of SiC MOSFET in Switching Conditions. <i>IEEE Electron Device Letters</i> , 2014, 35, 1284-1286.	2.2	96
8	ON-state characteristics of proton irradiated 4H-SiC Schottky diode: The calibration of model parameters for device simulation. <i>Solid-State Electronics</i> , 2014, 94, 32-38.	0.8	31
9	Temperature effects on the ruggedness of SiC Schottky diodes under surge current. <i>Microelectronics Reliability</i> , 2014, 54, 2207-2212.	0.9	6
10	Monolithically Integrated Temperature Sensor in Silicon Carbide Power MOSFETs. <i>IEEE Transactions on Power Electronics</i> , 2014, 29, 4970-4977.	5.4	33
11	Thermal Behavior of SiC Power Diodes. <i>ECS Transactions</i> , 2013, 50, 399-410.	0.3	1
12	Effect of the Growth Conditions on the Properties of Nitrided Oxides Grown by RTP for 4H-SiC p-Channel MOSFETs Fabrication. <i>Journal of the Electrochemical Society</i> , 2012, 159, H516-H521.	1.3	1
13	Study of 4H-SiC JBS Diodes Fabricated with Tungsten Schottky Barrier. <i>Journal of Electronic Materials</i> , 2011, 40, 2355-2362.	1.0	16
14	Rapid and Efficient Oxidation Process of SiC by <i>In Situ</i> Multiple RTP Steps. <i>Materials Science Forum</i> , 2010, 645-648, 817-820.	0.3	5
15	Comparaison de diodes SiC-4H Schottky et bipolaires 3 kV-20 A. <i>Revue Internationale De Génie Électrique</i> , 2009, 12, 225-236.	0.0	0
16	High Temperature Capability of High Voltage 4H-SiC JBS. <i>Materials Science Forum</i> , 0, 711, 124-128.	0.3	2
17	Integration of Temperature and Current Sensors in 4H-SiC VDMOS. <i>Materials Science Forum</i> , 0, 717-720, 1093-1096.	0.3	1
18	Gate Oxide Stability of 4H-SiC MOSFETs under On/Off-State Bias-Temperature Stress. <i>Materials Science Forum</i> , 0, 740-742, 553-556.	0.3	5

#	ARTICLE	IF	CITATIONS
19	Radiation Defects Produced in 4H-SiC Epilayers by Proton and Alpha-Particle Irradiation. Materials Science Forum, 0, 740-742, 661-664.	0.3	15
20	Edge Termination Design Improvements for 10 kV 4H-SiC Bipolar Diodes. Materials Science Forum, 0, 740-742, 609-612.	0.3	5
21	Study of 4H-SiC Schottky Diode Designs for 3.3kV Applications. Materials Science Forum, 0, 778-780, 795-799.	0.3	17
22	Comparison of 5kV SiC JBS and PiN Diodes. Materials Science Forum, 0, 778-780, 867-870.	0.3	4
23	Studies on Floating Contact Press-Pack Diodes Surge Current Capability. Materials Science Forum, 0, 858, 1053-1056.	0.3	1
24	Impact of Channel Mobility Improvement Using Boron Diffusion on Different Power MOSFETs Voltage Classes. Materials Science Forum, 0, 897, 537-540.	0.3	0